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•	Meets or Exceeds the Requirements of ANSI EIA/TIA-232-E and ITU V.28	DB PACKAGE (TOP VIEW)
٠	Operates With Single 3.3-V Power Supply	V_{DD} $\begin{bmatrix} 1 \\ 28 \end{bmatrix}$ C3+
٠	LinBiCMOS™ Process Technology	V _{DD} 1 28 C3+ C2+ 2 27 GND
٠	Three Drivers and Five Receivers	V_{CC} 3 26 C3-
	±30-V Input Levels (Receiver)	C2-[4 25] V _{SS}
•	ESD Protection on RS-232 Lines Exceeds	GND [] 5 24 [] C1 –
	6 kV Per MIL-STD-883C, Method 3015	C1+[] 6 23[] STBY
•	Applications	
-	– EIA/TIA-232 Interface	
	 Battery-Powered Systems 	
	- Notebook PC	ROUT1 🛛 10 🛛 19 🗍 RIN1
	- Computers	ROUT2[] 11 18]] RIN2
	– Terminals	ROUT3 12 17 RIN3
	– Modems	ROUT4 🛛 ¹³ 16 🗍 RIN4
•		ROUT5 14 ¹⁵ RIN5
	Voltage Converter Operates With Low	
	Capacitance 0.47 μ F Min	[†] The DB package is only available in left-end taped and

 Functionally Compatible With the SN75LV4737A

The DB package is only available in left-end taped and reeled (SN75LV4735DBLE).

description

The SN75LV4735[†] is a low-power 3.3-V multichannel RS-232 line driver/receiver. It includes three independent RS-232 drivers and five independent RS-232 receivers. It is designed to operate off a single 3.3-V supply and has an internal switched-capacitor voltage converter to generate the RS-232 output levels. The SN75LV4735 provides a single chip, single 3.3-V supply interface between the asynchronous communications element (ACE or UART) and the serial-port connector of the data terminal equipment (DTE). This device has been designed to conform to standard ANSI EIA/TIA-232-E.

The switched-capacitor voltage converter of the SN75LV4735 uses five small external capacitors to generate the positive and negative voltages required by EIA/TIA-232-E line drivers from a single 3.3-V input. The drivers feature output slew-rate limiting to eliminate the need for external filter capacitors. The receivers can accept \pm 30 V without damage.

The device also features a reduced power or standby mode that cuts the quiescent power to the integrated circuits when not transmitting data between the CPU and peripheral equipment. The STBY input is driven high for standby (reduced power) mode and driven low for normal operating mode. When in the standby mode, all driver outputs (DOUT1–3) and receiver outputs (ROUT1–5) are in the high-impedance state. If the standby feature is not used in an application, STBY should be tied to GND.

The SN75LV4735 has been designed using LinBiCMOS[™] technology and cells contained in the Texas Instruments LinASIC[™] library. The SN75LV4735 is characterized for operation from 0°C to 70°C.



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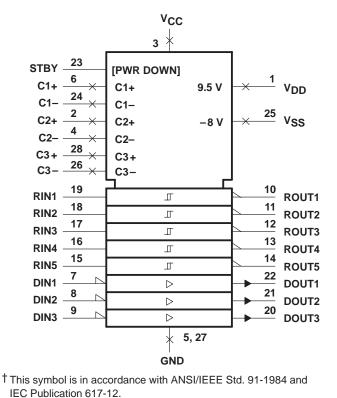
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

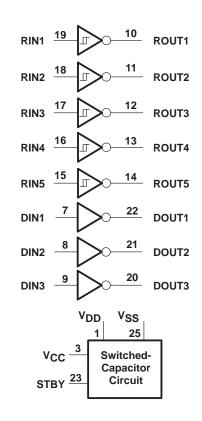


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logic symbol[†]





logic diagram (positive logic)

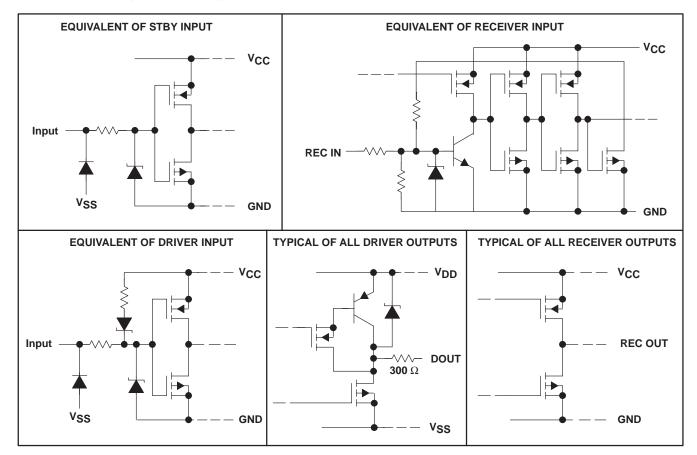
Function Tables

	EACH DR	RIVER		EACH RECEIVER				
INP	UTS			INP	UTS	OUTPUT		
DIN	STBY	OUTPUT		RIN	STBY	OUTPUT		
Х	Н	Z		Х	Н	Z		
L	L	Н		L	L	Н		
Н	L	L		Н	L	L		
Open	L	L		Open	L	Н		

H = high level, L = low level, X = irrelevant, Z = high impedance (off)



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schematics of inputs and outputs

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V _{CC}	
Positive output supply voltage, V _{DD} (see Note 1)	15 V
Negative output supply voltage, V _{SS}	–15 V
Input voltage range, VI: DIN1-DIN3, STBY	
RIN1-RIN5	
Output voltage range, V _O : DOUT1–DOUT3	$ V_{SS} - 0.3 V$ to $V_{DD} + 0.3 V$
ROUT1-ROUT5	
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{stg}	−65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

 [†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
 NOTE 1: All voltages are with respect to network GND.

DISSIPATION RATING TABLE							
PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING				
DB 668 mW		5.3 mW/°C	430 mW				



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recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}		3	3.3	3.6	V
Positive output supply voltage, V_{DD}		8	10		V
Negative output supply voltage, V_{SS}		-7	-8		V
Input voltage, VI (see Note 2)	RIN(1-5)			±30	V
High-level input voltage, VIH		2			v
Low-level input voltage, VIL	DIN(1–3), STBY			0.8	v
External capacitor		0.47	1		μF
Operating free-air temperature, T_A		0		70	°C

NOTE 2: The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only. For example, if -10 V is a maximum, the typical value is a more negative voltage.

supply currents

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
ICC	Supply current from V_{CC} (normal operating mode)	No load, STBY AT 0 V, All other inputs open		8.5	20	mA
ICC(SB)	Supply current (standby mode)	No load, STBY at V _{CC} , All other inputs open			10	μA



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DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)

	PARAMETER			TEST CONDITIONS		TYP†	MAX	UNIT
VOH	High-level output voltage		$R_L = 3 k\Omega$		5.5	7		V
VOL	V _{OL} Low-level output voltage (see Note 2)		$R_L = 3 k\Omega$			-5.5	-5	V
Чн	H High-level input current		V _I at V _{CC}				1	μΑ
	Low-level input current	STBY	V _I at GND				-1	μΑ
11		Other inputs	V _I at GND				-10	μΑ
IOS(H)	High-level short-circuit output current (see Not	e 3)	V _{CC} = 3.6 V,	VO = 0		-10	-20	mA
IOS(L)	Low-level short-circuit output current (see Note	e 3)	V _{CC} = 3.6 V,	$V_{O} = 0$		10	20	mA
rO	Output resistance		$V_{CC} = V_{DD} = V_{SS}$ $V_{O} = -2 V$ to 2 V,	s = 0, See Note 4	300			Ω

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

NOTES: 2. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only.

3. Not more than one output should be shorted at one time.

4. Test conditions are those specified by EIA/TIA-232-E.

switching characteristics, V_{CC} = 3.3 V \pm 0.3 V, T_A = 0°C to 70°C

	PARAMETER	TEST CON	TEST CONDITIONS			MAX	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	$R_{L} = 3 k\Omega$ to GND,	C _L = 50 pF,	200	400	600	ns
^t PHL	Propagation delay time, high- to low-level output	See Figure 2		100	200	350	ns
tPZL	Output enable time to low level (see Note 5)	$R_L = 3 k\Omega$ to GND, $C_L = 50 pR$ See Figure 3	С _L = 50 рF,		3	7	ms
^t PZH	Output enable time to high level (see Note 5)				1	5	ms
^t PHZ	Output disable time from high level (see Note 5)				1	3	μs
t _{PLZ}	Output disable time from low level (see Note 5)				0.5	3	μs
SR	Output slew rate (see Note 6)	$R_L = 3 k\Omega$ to 7 kΩ, See Figure 2	C _L = 50 pF,	3		30	V/µs
SR(tr)	Transition-region slew rate	$R_L = 3 k\Omega$ to GND, See Figure 4	C _L = 2500 pF,		3		V/µs

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

NOTES: 5. Output enable occurs when STBY is driven low. Output disable occurs when STBY is driven high.

 Measured between 3-V and –3-V points of output waveform (EIA/TIA-232-E conditions); all unused inputs are tied either high or low.



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RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CON	DITIONS	MIN	TYP†	MAX	UNIT
VIT+	Positive-going input threshold voltage				2.2	2.6	V
V_{IT-}	Negative-going input threshold voltage			0.6	1		V
V _{hys}	Input hysteresis voltage (VIT+ - VIT-)			0.5	1.2	1.8	V
VOH	High-level output voltage	$I_{OH} = -2 \text{ mA},$	See Note 7	2.4	2.6		V
VOL	Low-level output voltage	$I_{OL} = 2 \text{ mA}$			0.2	0.4	V
rj	Input resistance	$V_I = \pm 3 \text{ V to } \pm 25 \text{ V}$		3	5	7	kΩ

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

NOTE 7: If the inputs are left unconnected, the receiver interprets this as an input low, and the receiver outputs remain in the high state.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$

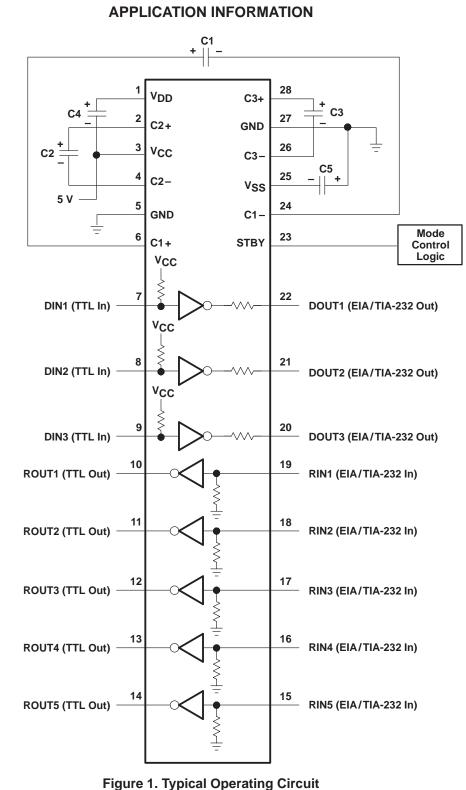
	PARAMETER	TEST CONI	DITIONS	MIN	TYP†	MAX	UNIT
^t PLH	Propagation delay time, low- to high-level output	$R_L = 3 k\Omega$ to GND,	See Figure 5	45	80	130	ns
^t PHL	Propagation delay time, high- to low-level output			70	100	170	ns
^t PZL	Output enable time to low level (see Note 5)	$R_L = 3 k\Omega$ to GND,	See Figure 6		160	250	ns
^t PZH	Output enable time to high level (see Note 5)				4	10	μs
^t PHZ	Output disable time from high level (see Note 5)				300	500	ns
^t PLZ	Output disable time from low level (see Note 5)				140	200	ns

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

NOTE 5: Output enable occurs when STBY is driven low. Output disable occurs when STBY input is driven high.

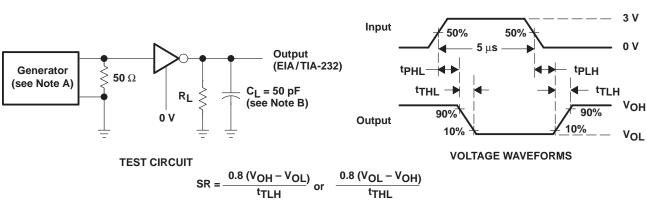


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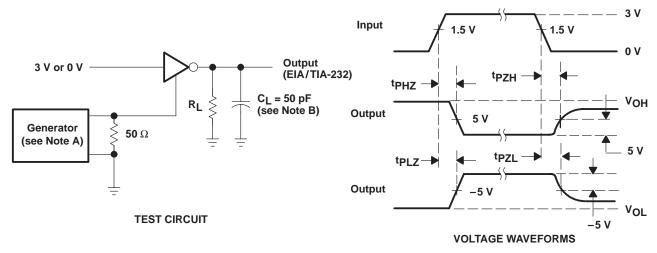
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PARAMETER MEASUREMENT INFORMATION

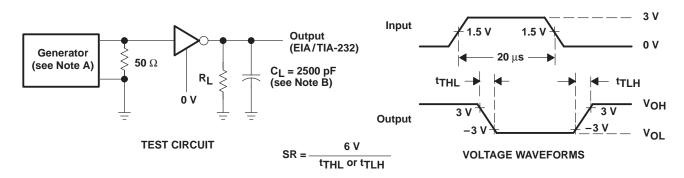
NOTES: A. The pulse generator has the following characteristics: 50% duty cycle, $t_f \le 10$ ns, $t_f = 10$ ns. B. CL includes probe and jig capacitance.





NOTES: A. The pulse generator has the following characteristics: 50% duty cycle, $t_f \le 10$ ns, $t_f = 10$ ns. B. CL includes probe and jig capacitance.





NOTES: A. The pulse generator has the following characteristics: 50% duty cycle, $t_{f} \le 10$ ns. $t_{f} = 10$ ns.

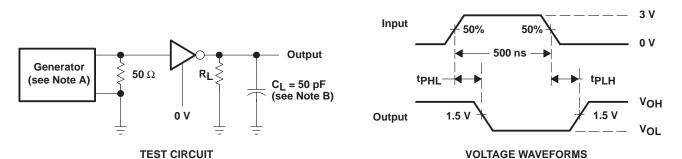
B. CL includes probe and jig capacitance.

Figure 4. Driver Test Circuit and Voltage Waveforms, Slew Rate at 20-µs Input



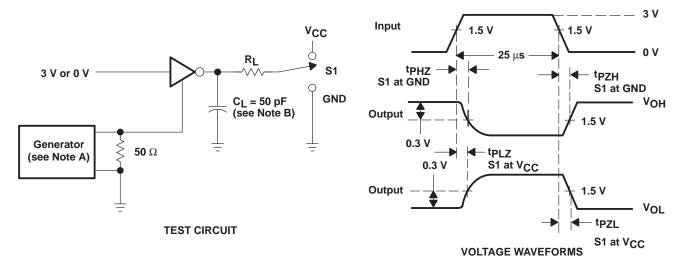
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PARAMETER MEASUREMENT INFORMATION



NOTES: A. The pulse generator has the following characteristics: PRR = 1 MHz, 50% duty cycle, $t_f \le 10$ ns, $t_f = 10$ ns. B. C₁ includes probe and jig capacitance.





NOTES: A. The pulse generator has the following characteristics: PRR = 1 MHz, 50% duty cycle, $t_f \le 10$ ns, $t_f = 10$ ns. B. C₁ includes probe and jig capacitance.

Figure 6. Receiver Test Circuit and Voltage Waveforms Enable and Disable Times

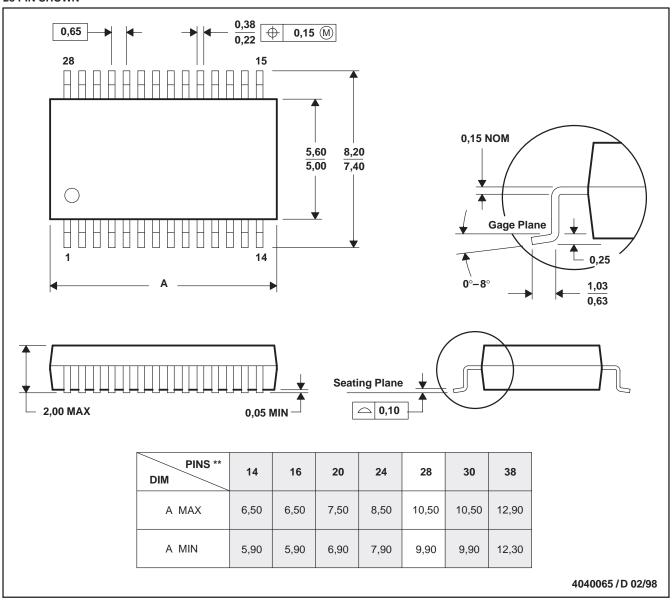


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MECHANICAL DATA

PLASTIC SMALL-OUTLINE PACKAGE

DB (R-PDSO-G**) 28 PIN SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150



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